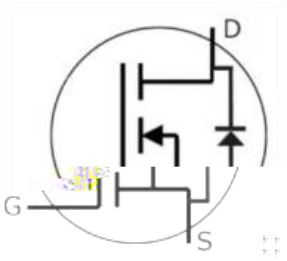
-
-
-
-
-

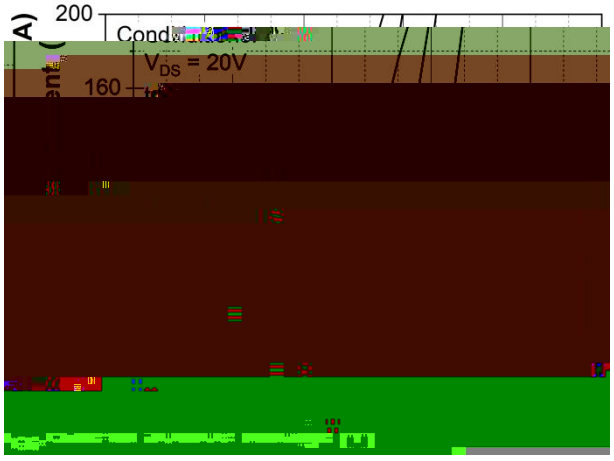

D
G
S

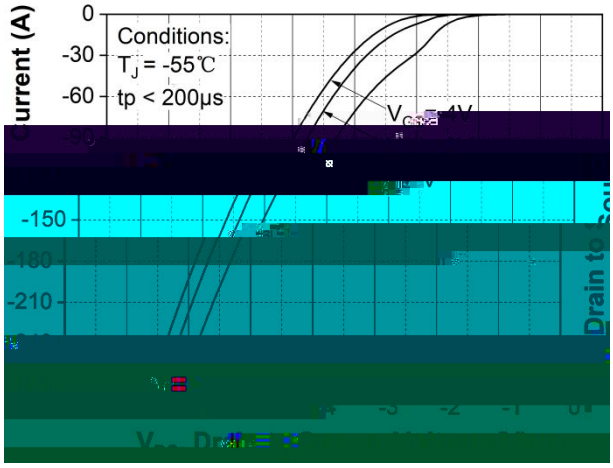
-
-
-
-
-

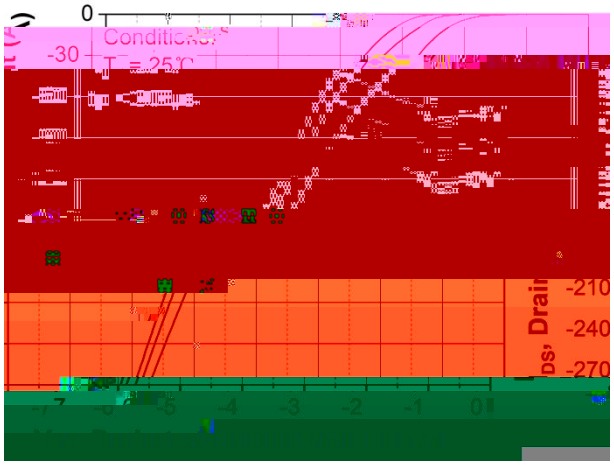
-
-
-
-

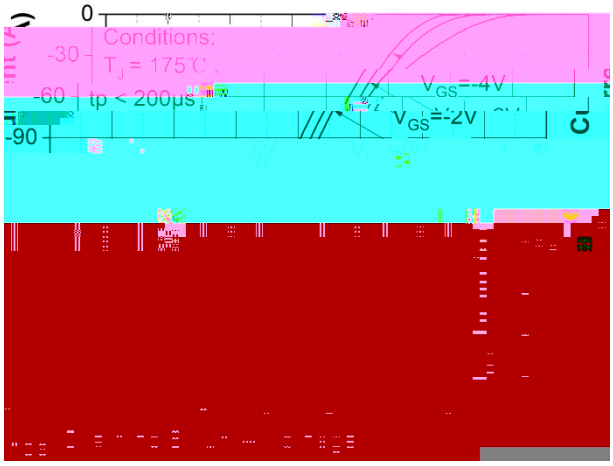
		≤		

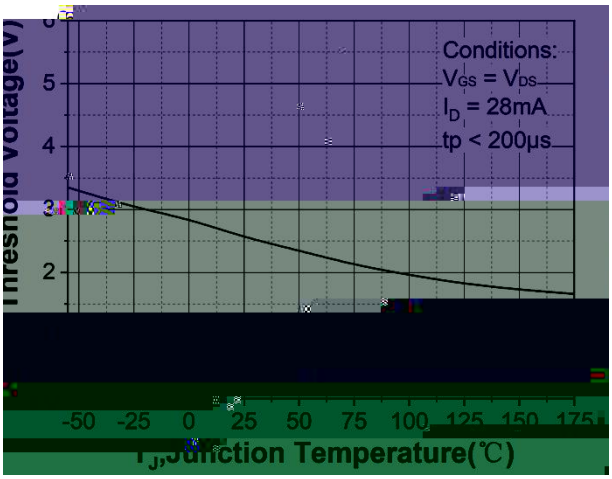


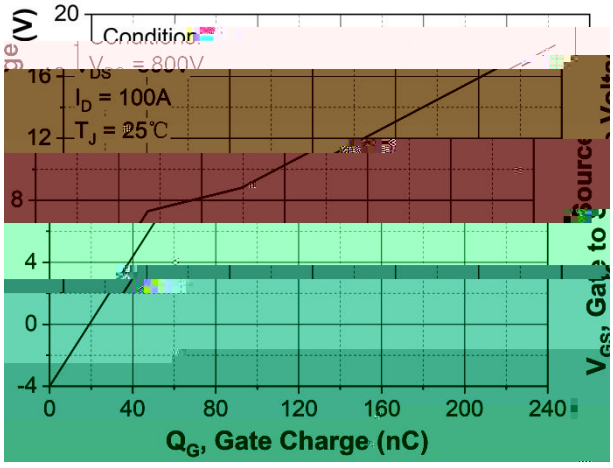

200
160
V_{DS} = 20V


0
-30
-60
-150
-180
-210
Conditions:
T_J = -55℃
tp < 200μs
V_{GS}=-4V

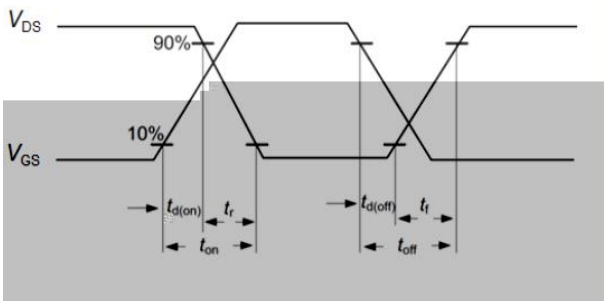

0
-30
-210
-240
-270
Conditions:
T_J = 25℃

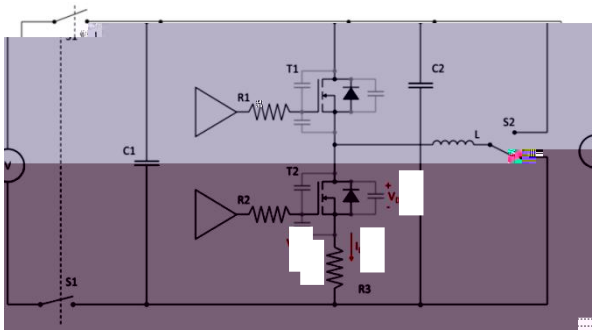

0
-30
-60
-90
Conditions:
T_J = 175℃
tp < 200μs
V_{GS}=-4V
V_{GS}=-2V

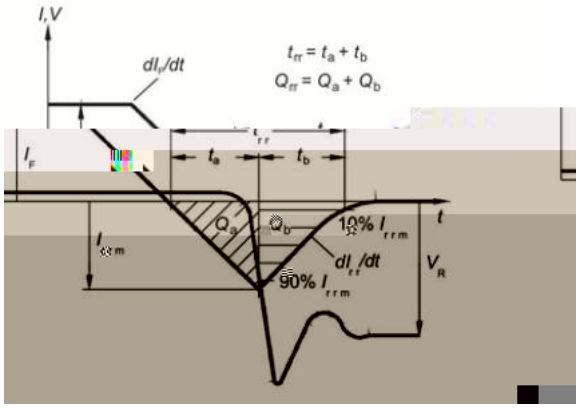

5
4
3
2
-50 -25 0 25 50 75 100 125 150 175
Conditions:
V_{GS} = V_{DS}
I_D = 28mA
tp < 200μs
T_J,Junction Temperature(℃)


20
16
12
8
4
0
-4
0 40 80 120 160 200 240
V_{DS} = 800V
I_D = 100A
T_J = 25℃
Q_G, Gate Charge (nC)




V_{DS}
90%
10%
V_{GS}
$t_{d(on)}$
t_r
t_{on}
$t_{d(off)}$
t_f
t_{off}


T1
C2
R1
S2
L
C1
T2
R2
R3
S1


I,V
dI_F/dt
$t_{rr} = t_a + t_b$
$Q_{rr} = Q_a + Q_b$
I_F
t_a
t_b
Q_a
Q_b
10% I_{rrm}
I_{rrm}
dI_{rr}/dt
90% I_{rrm}
V_R
t

		——	——
		——	——
		——	——
		——	——
		——	——
		——	——
		——	——
			——

K V

L P

WñB ð Rp•'ai G

) L